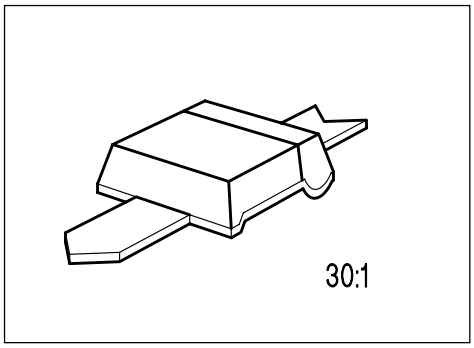
SIEMENS

Silicon PIN Diodes

BXY 42BA-S
BXY 42BB-S

- Beam lead version
- Fast switching



ESD: **E**lectro**s**tatic **d**ischarge sensitive device, observe handling precautions!

Type	Marking	Ordering Code	Pin Configuration	Package[1)]
BXY 42BA-S	–	Q62702-X151	Pointed cathode	S
BXY 42BB-S		Q62702-X159		

Maximum Ratings

Parameter	Symbol	Values		Unit
		BXY 42BA-S	BXY 42BB-S	
Reverse voltage	V_R	50	30	V
Junction temperature	T_j	175		°C
Storage temperature range	T_{stg}	– 55 … + 150		
Operating temperature range	T_{op}	– 55 … + 150		

1) For detailed information see chapter Package Outlines.

Electrical Characteristics
at T_A = 25 °C, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Breakdown voltage I_R = 10 µA	$V_{(BR)}$	50	–	–	V
Forward voltage I_F = 50 mA	V_F	–	1.0	–	
Reverse current V_R = 40 V	I_R	–	–	5	nA
Storage time I_F = 10 mA, V_R = 10 V	t_s	–	3	–	ns
Diode capacitance V_R = 30 V, f = 1 MHz	C_T	–	–	0.08	pF
Charge carrier life time I_F = 10 mA, I_R = 6 mA	τ_L	–	30	–	ns
Forward resistance f= 100 MHz, I_F = 10 mA	r_f	–	1.8	–	Ω

Electrical Characteristics
at T_A = 25 °C, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Breakdown voltage I_R = 10 µA	$V_{(BR)}$	30	–	–	V
Forward voltage I_F = 50 mA	V_F	–	1.1	–	
Reverse current V_R = 20 V	I_R	–	–	5	nA
Storage time I_F = 10 mA, V_R = 10 V	t_s	–	2	–	ns
Diode capacitance V_R = 20 V, f = 1 MHz	C_T	–	–	0.15	pF
Charge carrier life time I_F = 10 mA, I_R = 6 mA	τ_L	–	20	–	ns
Forward resistance f= 100 MHz, I_F = 10 mA	r_f	–	1.3	–	Ω

littlediode
COMPONENTS FOR ALL

Littlediode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.